

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning on page 6, line 20 and ending on page 7, line 14, with the following amended paragraph:

FIG. 1 is a sectional view of the CMOS image sensor produced by the producing method of a CMOS image sensor according to Embodiment 1 of the present invention. A photodiode 1 is formed by stacking an N type diffused layer 12 and a P type diffused layer 13, and buried together with an N-type MOS transistor 16 in the top surface of a P well 11 formed over a common substrate 10. And an oxide film 2 (a ~~part of a first~~ type insulating film) is formed such that the oxide film covers the surface of the photodiode 1, a nitride film 3 (a ~~part of a second~~ type insulating film) is formed over the oxide film 2, an oxide film 4 (a ~~part of the first~~ type insulating film) is formed over the nitride film 3, and a nitride film 5 (a ~~part of the second~~ type insulating film) is formed over the oxide film 4. A contact interlayer oxide film 6 (insulating layer) is formed over the nitride film 5, and contact holes 7 are provided through the contact interlayer oxide film. A first interlayer insulating layer 6a is formed over the surface of the contact interlayer oxide film 6, and a first layer aluminum film 19 is buried in the bottom surface of the first interlayer insulating layer 6a. A second interlayer insulating layer 6b is formed over the surface of the first layer insulating layer 6a, and a second layer aluminum film 20 is buried in the bottom surface of the second interlayer insulating layer 6b. Optionally, the common substrate 10 may be formed of N type or P type silicon. The antireflection film of the photodiode 1 is formed of the stacked oxide film 2, nitride film 3, oxide film 4, and nitride film 5.